

NPN resistor-equipped transistor; R1 = 4.7 kΩ, R2 = 47 kΩRev. 1 — 11 June 2012Product data s

Product data sheet

#### 1. **Product profile**

### **1.1 General description**

NPN Resistor-Equipped Transistor (RET) in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

PNP complement: PDTA143ZMB.

### 1.2 Features and benefits

- 100 mA output current capability
- Reduces component count
- Built-in bias resistors
- Reduces pick and place costs

### **1.3 Applications**

- Low-current peripheral driver
- Control of IC inputs

- Simplifies circuit design
- AEC-Q101 qualified
- Leadless ultra small SMD plastic package
- Low package height of 0.37 mm
- Replaces general-purpose transistors in digital applications
- Mobile applications

### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	50	V
lo	output current		-	-	100	mA
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		8	10	12	



NPN resistor-equipped transistor;  $R1 = 4.7 \text{ k}\Omega$ ,  $R2 = 47 \text{ k}\Omega$ 

# 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	I	input (base)		
2	G	GND (emitter)		
3	0	output (collector)	2 Transparent top view SOT883B (DFN1006B-3)	1 R1 R2 R2 2 sym007

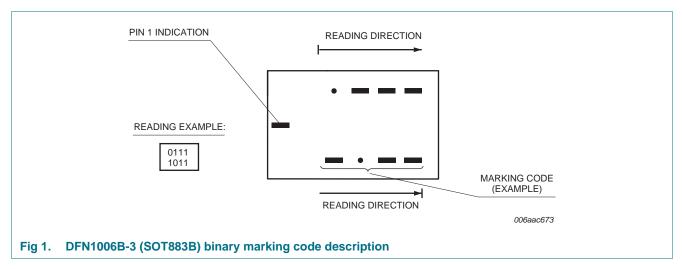
# 3. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
PDTC143ZMB	DFN1006B-3	Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B				

# 4. Marking

Table 4.	Marking o	odes
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Type number	Marking code
PDTC143ZMB	0001 0110



NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 

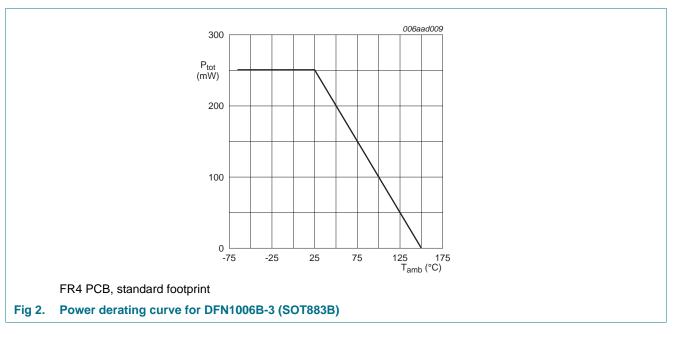
## 5. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Мах	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	5	V
VI	input voltage	positive		-	30	V
		negative		-	-5	V
lo	output current			-	100	mA
I <sub>CM</sub>	peak collector current	pulsed; t <sub>p</sub> ≤ 1 ms		-	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	<u>[1]</u>	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



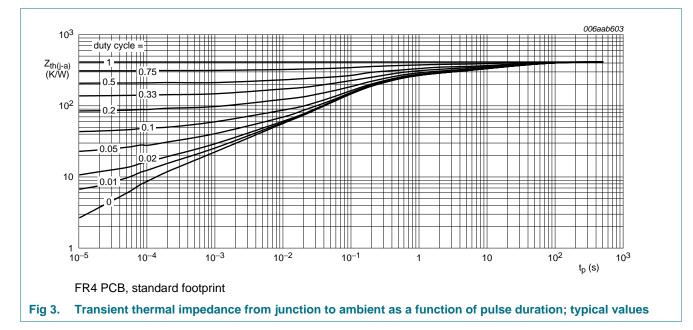
# 6. Thermal characteristics

Table 6.	Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	-	500	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

# PDTC143ZMB

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## 7. Characteristics

#### Table 7. Characteristics

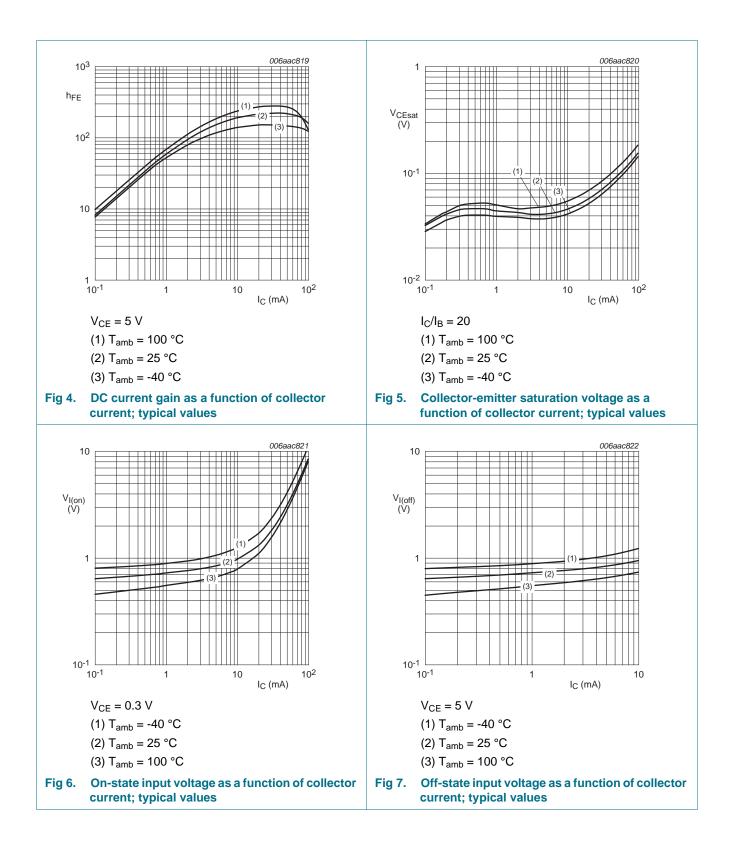
<b>A A A A A</b>	<b>D</b>				-		11.14
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 50 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$		-	-	100	nA
I <sub>CEO</sub>	collector-emitter cut-off	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{amb} = 25 \text{ °C}$		-	-	1	μA
	current	$V_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{j} = 150 ^{\circ}\text{C}$		-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB}$ = 5 V; $I_{C}$ = 0 A; $T_{amb}$ = 25 °C		-	-	170	μA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 5 V; I <sub>C</sub> = 10 mA; T <sub>amb</sub> = 25 °C		100	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C} = 5 \text{ mA}; I_{B} = 0.25 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	100	mV
V <sub>I(off)</sub>	off-state input voltage	$V_{CE}$ = 5 V; $I_{C}$ = 100 $\mu A;$ $T_{amb}$ = 25 $^{\circ}C$		-	0.6	0.5	V
V <sub>I(on)</sub>	on-state input voltage	$V_{CE}$ = 0.3 V; $I_{C}$ = 5 mA; $T_{amb}$ = 25 $^{\circ}C$		1.3	0.9	-	V
R1	bias resistor 1 (input)	T <sub>amb</sub> = 25 °C		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio			8	10	12	
C <sub>C</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	-	2.5	pF
f <sub>T</sub>	transition frequency	$V_{CE}$ = 5 V; I <sub>C</sub> = 10 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	<u>[1]</u>	-	230	-	MHz

[1] Characteristics of built-in transistor.

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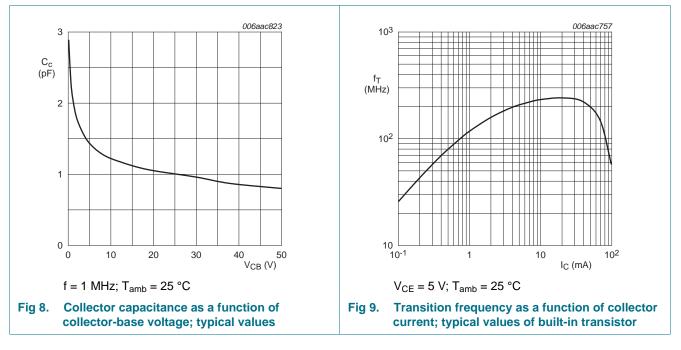
# PDTC143ZMB

NPN resistor-equipped transistor;  $R1 = 4.7 \text{ k}\Omega$ ,  $R2 = 47 \text{ k}\Omega$ 



### **NXP Semiconductors**

NPN resistor-equipped transistor; R1 = 4.7 k $\Omega$ , R2 = 47 k $\Omega$ 



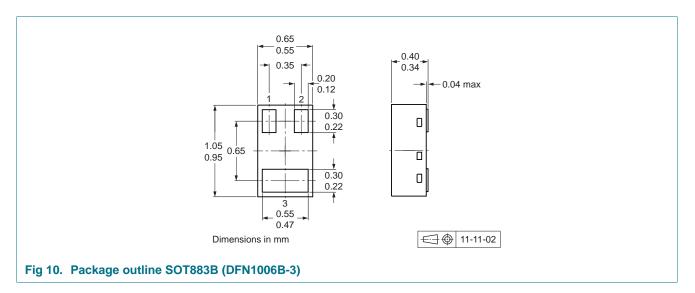
## 8. Test information

#### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

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#### **Package outline** 9.



# 10. Soldering

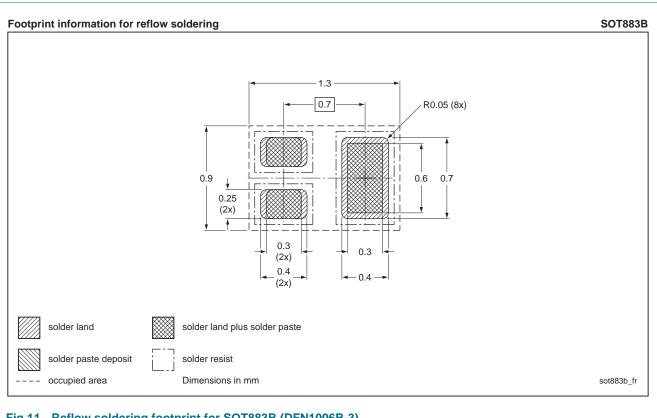


Fig 11. Reflow soldering footprint for SOT883B (DFN1006B-3)

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# **11. Revision history**

Table 8. Revision h	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTC143ZMB v.1	20120611	Product data sheet	-	-

NPN resistor-equipped transistor;  $R1 = 4.7 \text{ k}\Omega$ ,  $R2 = 47 \text{ k}\Omega$ 

## 12. Legal information

#### 12.1 Data sheet status

Document status[1] [2]	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions'

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Product data sheet

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